



N-Channel Enhancement-Mode Vertical DMOS FET

Features

- ▶ Low threshold
- ▶ High input impedance
- ▶ Low input capacitance
- ▶ Fast switching speeds
- ▶ Low on-resistance
- ▶ Free from secondary breakdown
- ▶ Low input and output leakage

Applications

- ▶ Logic level interfaces – ideal for TTL and CMOS
- ▶ Solid state relays
- ▶ Battery operated systems
- ▶ Photo voltaic drives
- ▶ Analog switches
- ▶ General purpose line drivers
- ▶ Telecom switches

General Description

This low threshold, enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Part Number	Package Option	Packing
TN2425N8-G	TO-243AA (SOT-89)	2000/Reel

-G denotes a lead (Pb)-free / RoHS compliant package.
Contact factory for Wafer / Die availability.
Devices in Wafer / Die form are lead (Pb)-free / RoHS compliant.

Product Summary

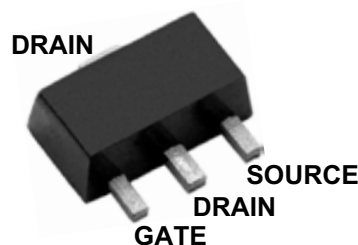
BV_{DSS}/BV_{DGS}	$R_{DS(ON)}$ (max)	I_{DSS} (min)
25V	3.58Ω	1.5A

Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	BV_{DSS}
Drain-to-gate voltage	BV_{DGS}
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Pin Configuration



TO-243AA (SOT-89)

Product Marking



W = Code for Week Sealed
— = "Green" Packaging

Package may or may not include the following marks: Si or

TO-243AA (SOT-89)

Typical Thermal Resistance

Package	θ_{JA}
TO-243AA (SOT-89)	133°C/W

Thermal Characteristics

Package	I_D (continuous) [†]	I_D (pulsed)	Power Dissipation @ $T_c = 25^\circ\text{C}$	$I_{DR}^\ddagger$	I_{DRM}
TO-243AA (SOT-89)	480mA	1.90A	1.6W [‡]	480mA	1.90A

Notes:

[†] I_D (continuous) is limited by max rated T_j .

[‡] $T_A = 25^\circ\text{C}$. Mounted on FR5 Board, 25mm x 25mm x 1.57mm. Significant P_D increase possible on ceramic substrate.

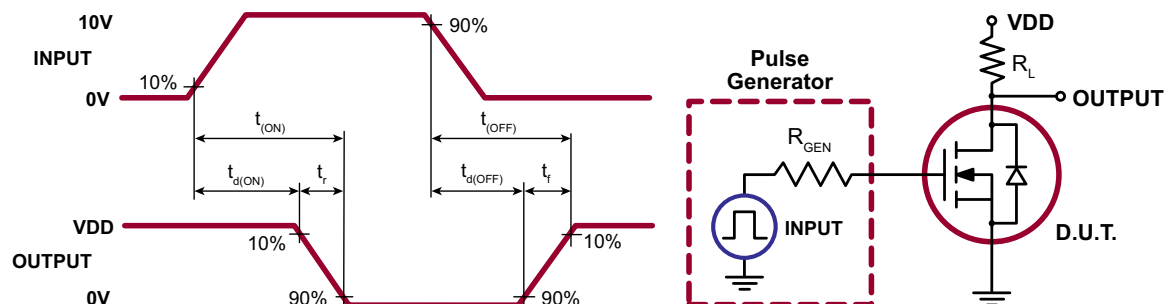
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Sym	Parameter	Min	Typ	Max	Units	Conditions
BV_{DSS}	Drain-to-source breakdown voltage	250	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$
$V_{GS(th)}$	Gate threshold voltage	0.8	-	2.5	V	$V_{GS} = V_{DS}, I_D = 1.0mA$
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with temperature	-	-	-5.5	mV/ $^\circ\text{C}$	$V_{GS} = V_{DS}, I_D = 1.0mA$
I_{GSS}	Gate body leakage	-	-	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
I_{DSS}	Zero gate voltage drain current	-	-	10	μA	$V_{GS} = 0V, V_{DS} = \text{Max Rating}$
		-	-	1.0	mA	$V_{DS} = 0.8\text{Max Rating}, V_{GS} = 0V, T_A = 125^\circ\text{C}$
$I_{D(ON)}$	On-state drain current	0.8	-	-	A	$V_{GS} = 4.5V, V_{DS} = 25V$
		1.5	-	-		$V_{GS} = 10V, V_{DS} = 25V$
$R_{DS(ON)}$	Static drain-to-source on-state resistance	-	-	6.0	Ω	$V_{GS} = 3.0V, I_D = 150mA$
		-	-	5.0		$V_{GS} = 4.5V, I_D = 250mA$
		-	-	3.5		$V_{GS} = 10V, I_D = 500mA$
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	-	1.7	%/ $^\circ\text{C}$	$V_{GS} = 10V, I_D = 500mA$
G_{FS}	Forward transconductance	500	-	-	mmho	$V_{DS} = 25V, I_D = 250mA$
C_{ISS}	Input capacitance	-	105	200	pF	$V_{GS} = 0V, V_{DS} = 25V, f = 1.0MHz$
C_{OSS}	Common source output capacitance	-	25	100		
C_{RSS}	Reverse transfer capacitance	-	7.0	40		
$t_{d(ON)}$	Turn-on delay time	-	5.0	15	ns	$V_{DD} = 25V, I_D = 500mA, R_{GEN} = 25\Omega$
t_r	Rise time	-	10	25		
$t_{d(OFF)}$	Turn-off delay time	-	25	35		
t_f	Fall time	-	5.0	15		
V_{SD}	Diode forward voltage drop	-	-	1.5	V	$V_{GS} = 0V, I_{SD} = 500mA$
t_{rr}	Reverse recovery time	-	300	-	ns	$V_{GS} = 0V, I_{SD} = 500mA$

Notes:

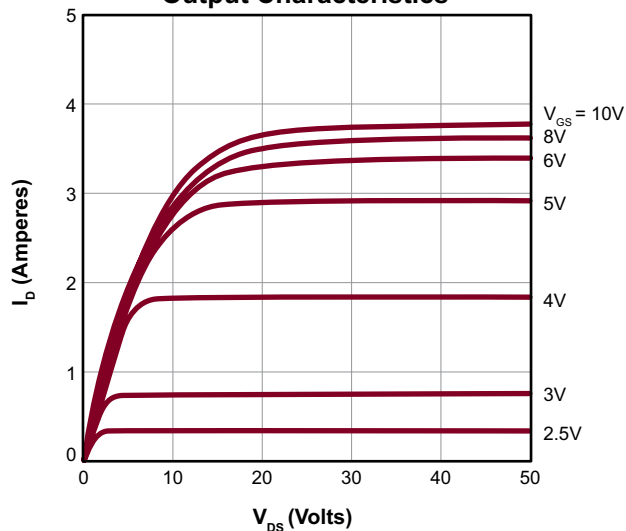
1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300 μs pulse, 2% duty cycle.)
2. All A.C. parameters sample tested.

Switching Waveforms and Test Circuit

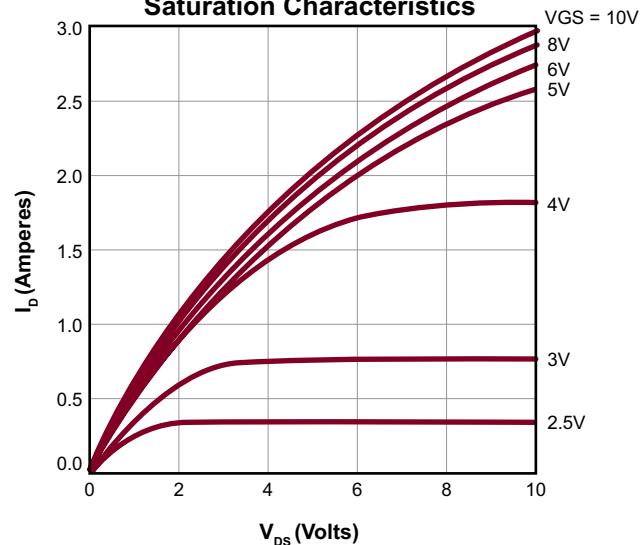


Typical Performance Curves

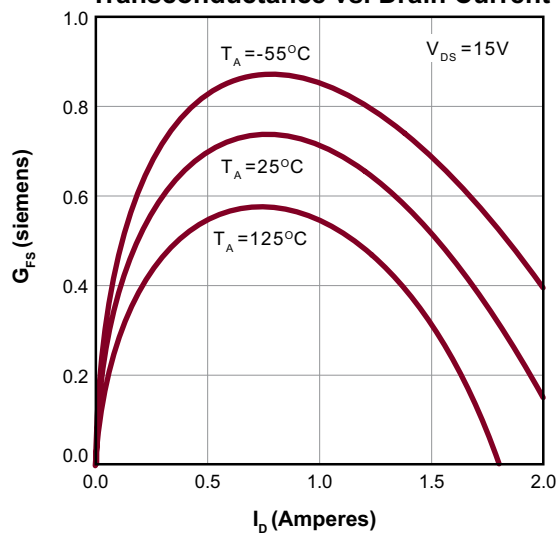
Output Characteristics



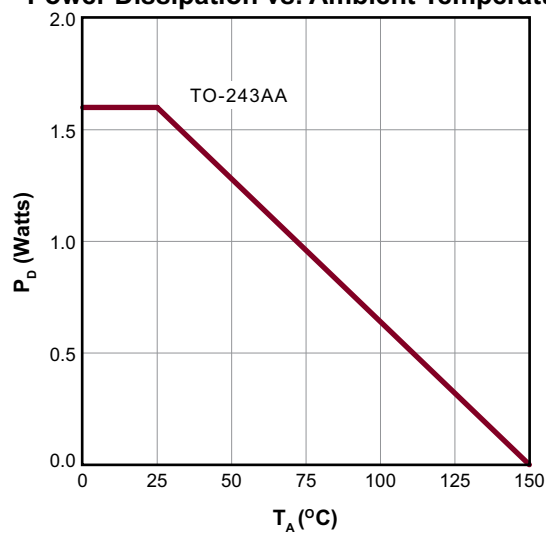
Saturation Characteristics



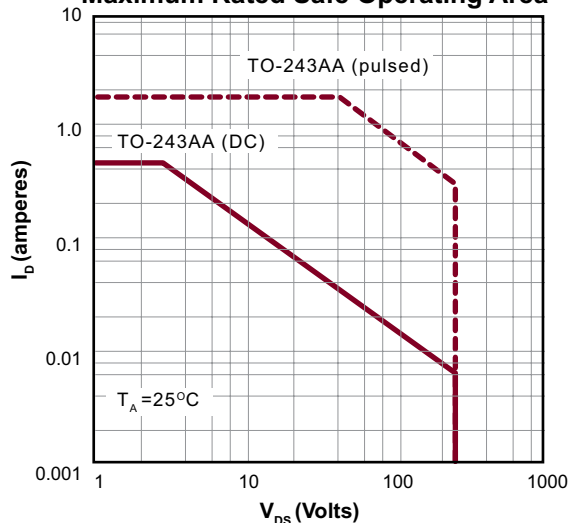
Transconductance vs. Drain Current



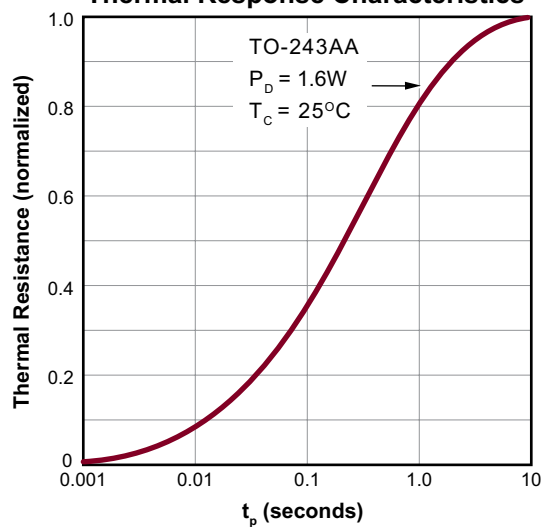
Power Dissipation vs. Ambient Temperature



Maximum Rated Safe Operating Area

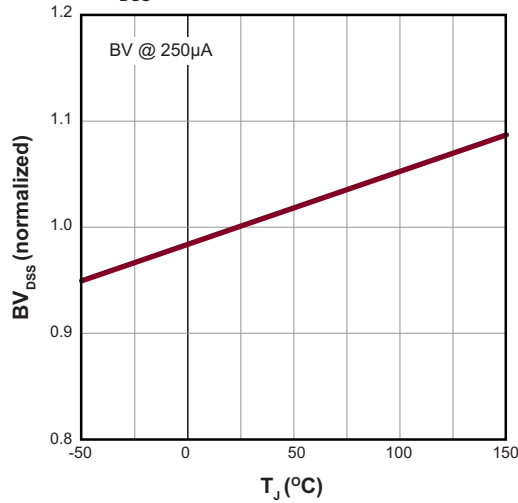


Thermal Response Characteristics

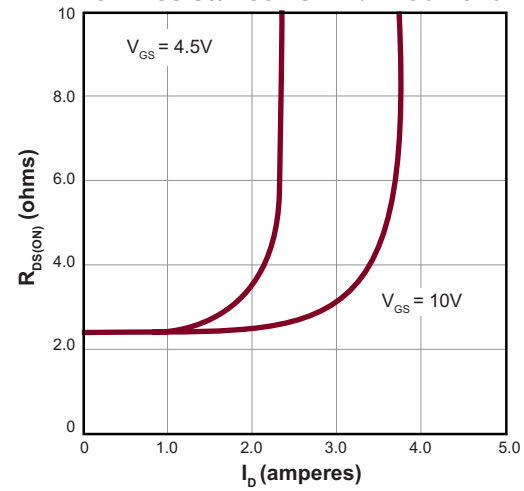


Typical Performance Curves (cont.)

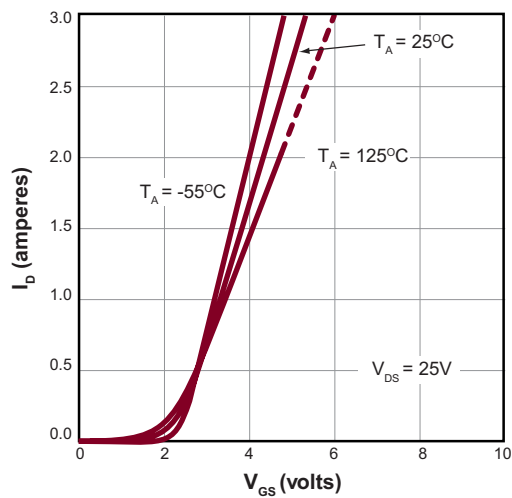
BV_{DSS} Variation with Temperature



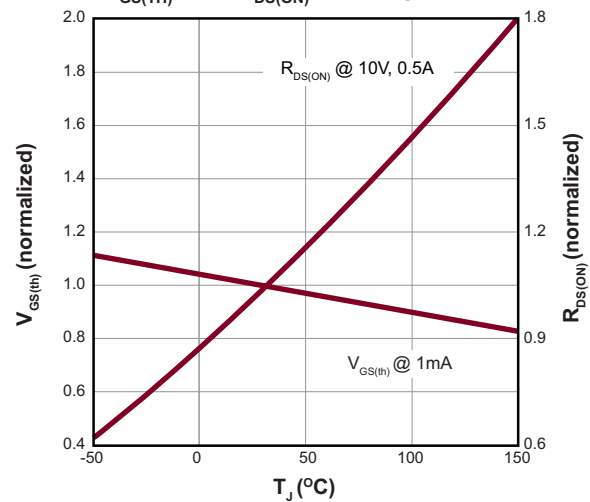
On Resistance vs. Drain Current



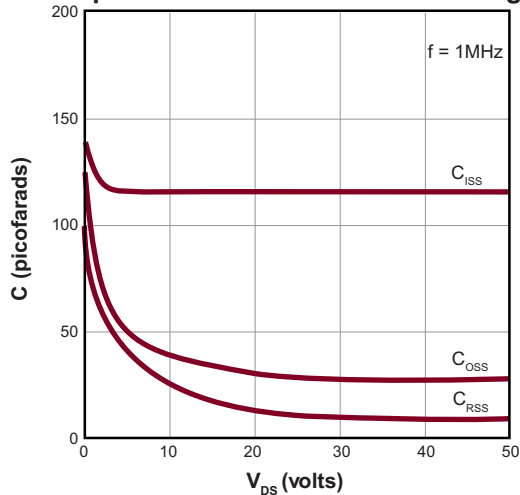
Transfer Characteristics



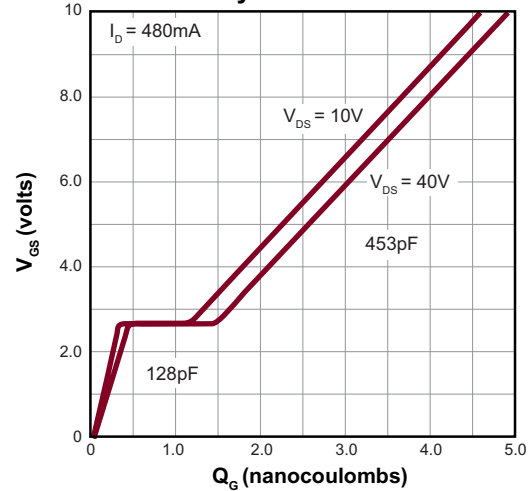
V_{GS(TH)} and R_{DS(ON)} w/ Temperature



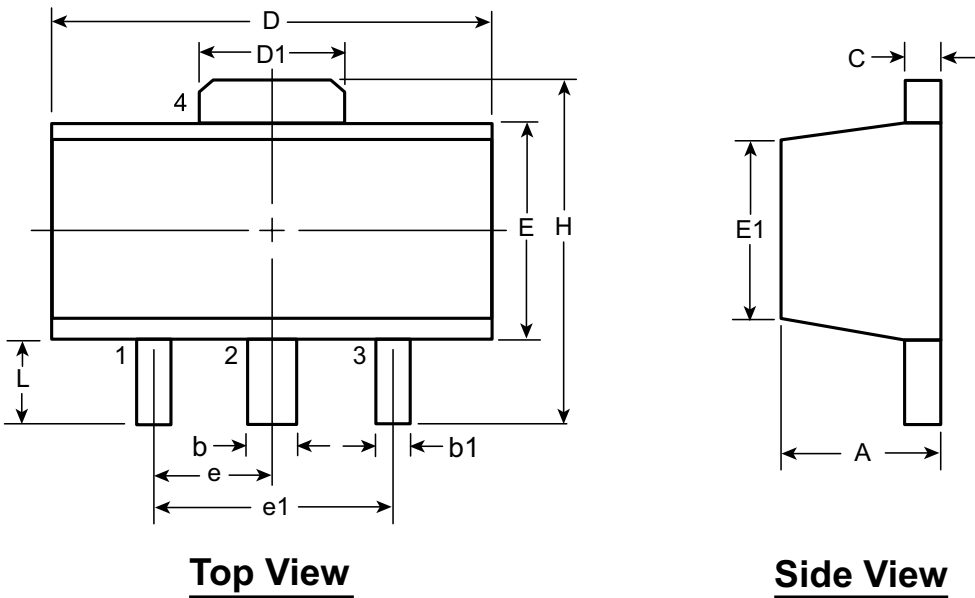
Capacitance vs. Drain Source Voltage



Gate Drive Dynamic Characteristics



3-Lead TO-243AA (SOT-89) Package Outline (N8)



Symbol		A	b	b1	C	D	D1	E	E1	e	e1	H	L
Dimensions (mm)	MIN	1.40	0.44	0.36	0.35	4.40	1.62	2.29	2.00†	1.50 BSC	3.00 BSC	3.94	0.73†
	NOM	-	-	-	-	-	-	-	-			-	-
	MAX	1.60	0.56	0.48	0.44	4.60	1.83	2.60	2.29			4.25	1.20

JEDEC Registration TO-243, Variation AA, Issue C, July 1986.

† This dimension differs from the JEDEC drawing

Drawings not to scale.

Supertex Doc. #: DSPD-3TO243AAN8, Version F111010.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <http://www.supertex.com/packaging.html>.)

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